

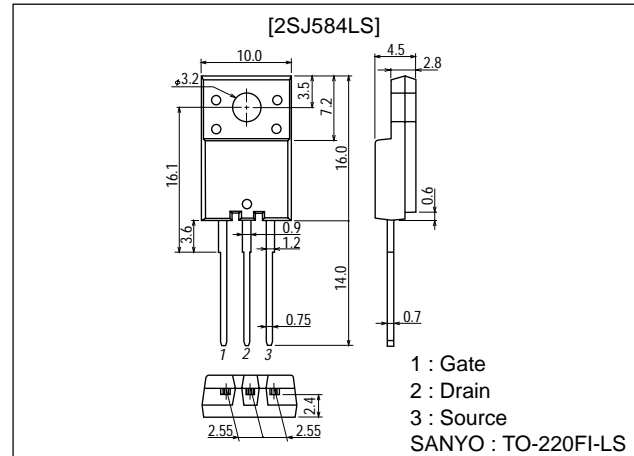
**2SJ584LS****Ultrahigh-Speed Switching Applications****Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- Micaless package facilitating mounting.

Package Dimensions

unit:mm

2078B

**Specifications****Absolute Maximum Ratings** at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-250	V
Gate-to-Source Voltage	V_{GS}		± 30	V
Drain Current (DC)	I_D		-4.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-18	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c = 25^\circ\text{C}$	25	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0$	-250			V
Gate-to-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$	± 30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -250\text{V}$, $V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 25\text{V}$, $V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-3.5		-5.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{V}$, $I_D = -2.5\text{A}$	1.5	2.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D = -2.5\text{A}$, $V_{GS} = -10\text{V}$		0.95	1.2	Ω

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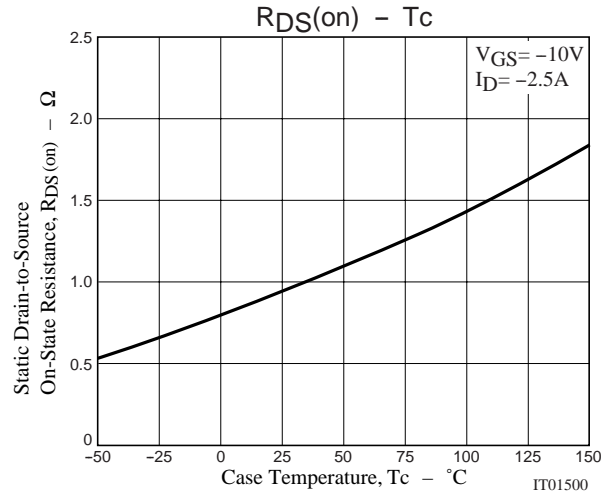
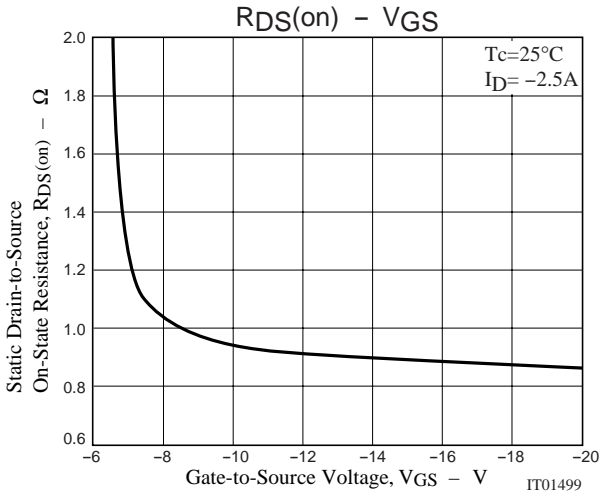
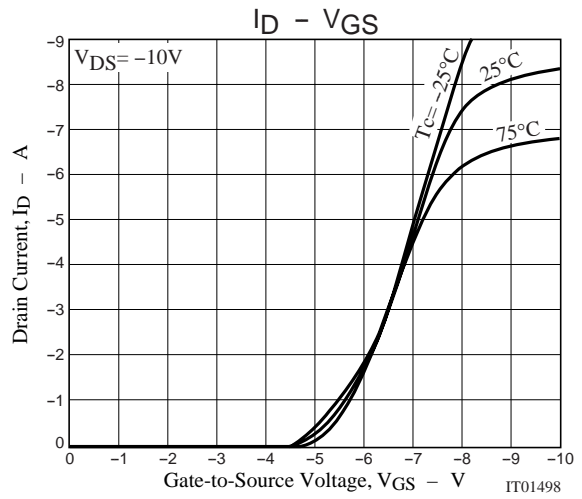
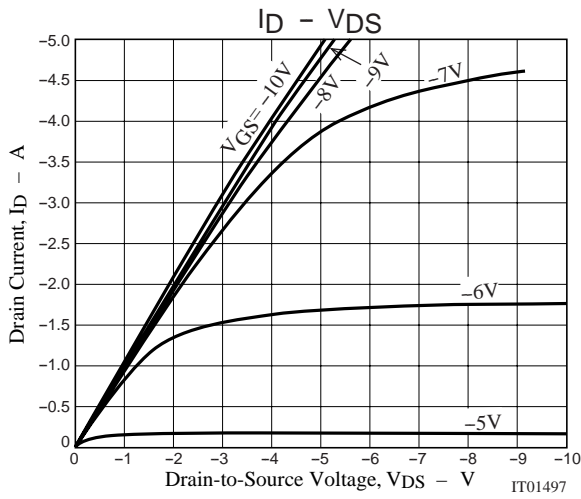
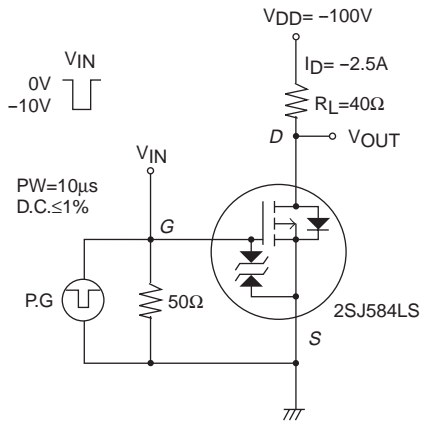
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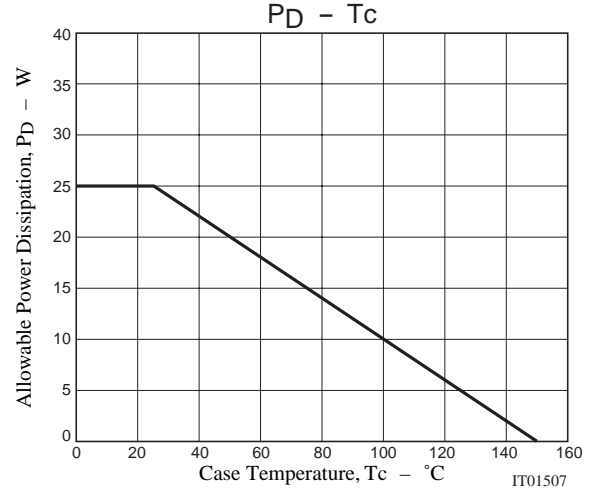
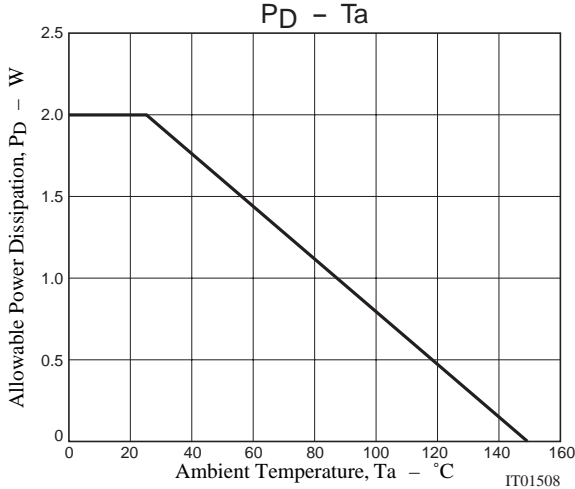
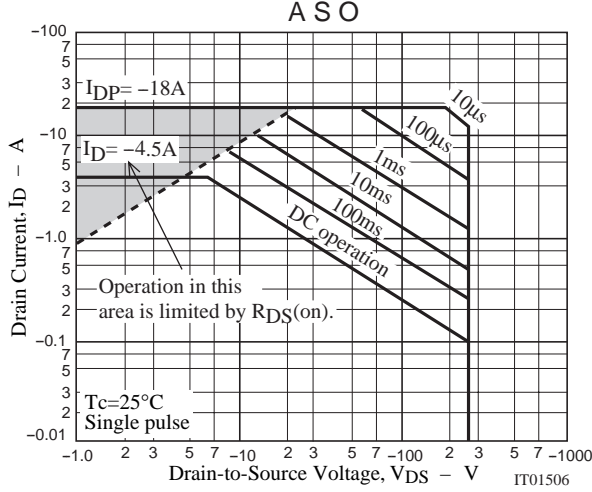
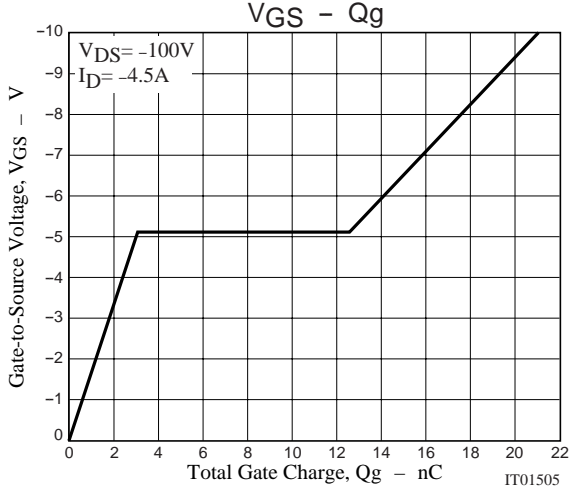
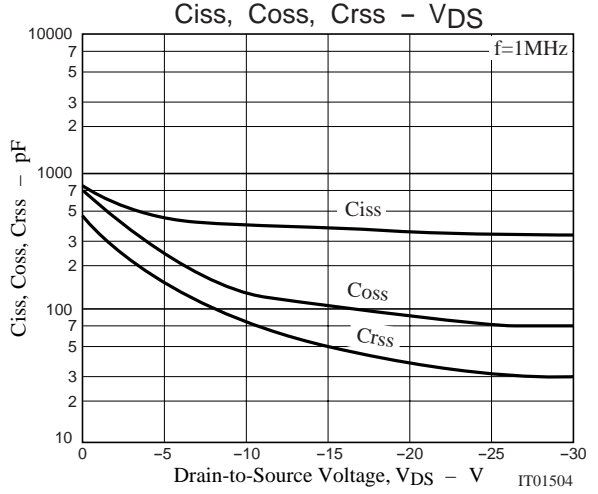
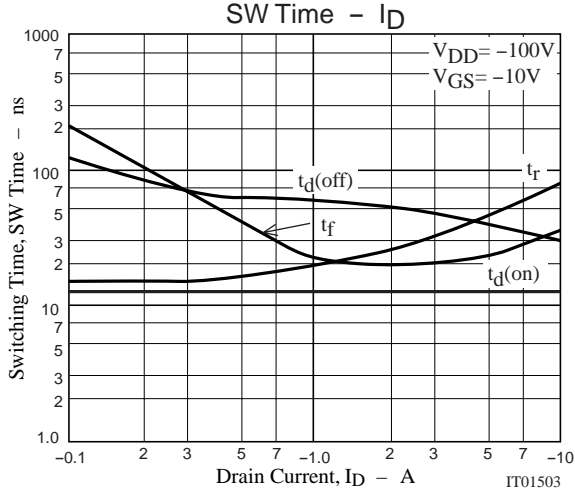
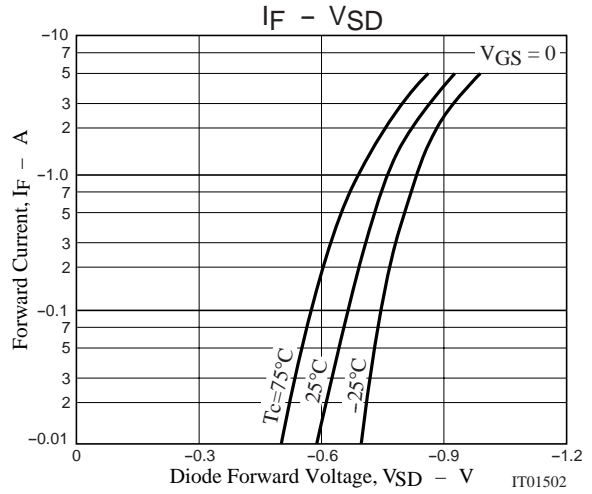
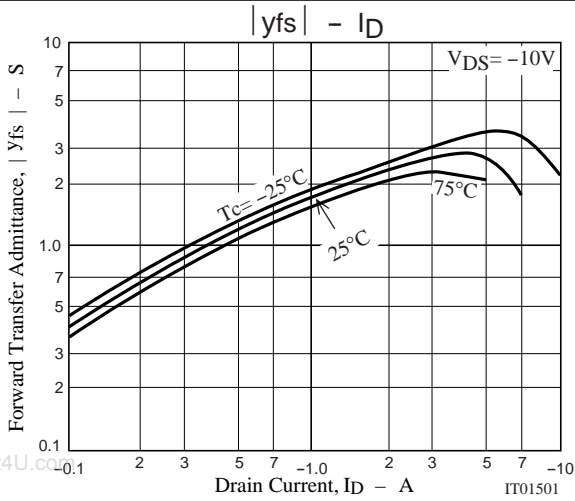
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	C_{iss}	$V_{DS}=-20V, f=1MHz$		450		pF
Output Capacitance	C_{oss}	$V_{DS}=-20V, f=1MHz$		120		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=-20V, f=1MHz$		50		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		12.5		ns
Rise Time	t_r	See specified Test Circuit		30		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		52		ns
Fall Time	t_f	See specified Test Circuit		21		ns
Total Gate Charge	Q_g	$V_{DS}=-100V, V_{GS}=-10V, I_D=-4.5A$		22		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-100V, V_{GS}=-10V, I_D=-4.5A$		3.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=-100V, V_{GS}=-10V, I_D=-4.5A$		11		nC
Diode Forward Voltage	V_{SD}	$I_S=-4.5A, V_{GS}=0$		-0.9	-1.5	V

Marking : J584

Switching Time Test Circuit



2SJ584LS



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